



# MEDIUM POWER COMPLEMENTRY DARLINGTON SILICON TRANSISTORS

PNP NPN 2N6040 2N6043 2N6041 2N6044 2N6042 2N6045



TO-220

T0-220 Leaded Plastic Package RoHS compliant

# **APPLICATIONS:**

Designed for general purpose amplifier and low-speed switching applications

# **ABSOLUTE MAXIMUM RATINGS** $(T_a = 25 \, ^{\circ}C)$

VALUE					
PARAMETER	SYMBOL	2N6040	2N6041	2N6042	UNIT
		2N6043	2N6044	2N6045	
Collector-Emitter Voltage	$V_{CEO}$	60	80	100	V
Collector-Base Voltage	$V_{CBO}$	60	80	100	V
Emitter-Base Voltage	$V_{EBO}$	5		V	
Collector Current-Continuous	I <sub>C</sub>	8.0		^	
Collector Current-Peak	I <sub>CM</sub>	16		A	
Base Current	$I_{B}$	120		mA	
Total Power Dissipation @ T <sub>C</sub> =25°C	В	75		W	
Derate above 25°C	P <sub>D</sub>	0.6		W/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150		°C	

# THERMAL RESISTANCE

	Junction to Case	$R_{\theta jc}$	1.67	°C/W
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PARAMETER	SYMBOL	L TEST CONDITION		VALUE		
PARAMETER	SYMBOL TEST CONDITION		MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Emitter Sustaining Voltage <sup>1</sup> 2N6040, 2N6043 2N6041, 2N6044 2N6042, 2N6045	$V_{\text{CEO(sus)}}$	I <sub>C</sub> = 30mA , I <sub>B</sub> =0	60 80 100			V
Collector Cutoff Current			100			
2N6040, 2N6043 2N6041, 2N6044 2N6042, 2N6045	I <sub>CEO</sub>	$V_{CE}$ =30V, $I_{B}$ =0 $V_{CE}$ =40V, $I_{B}$ =0 $V_{CE}$ =50V, $I_{B}$ =0			0.5 0.5 0.5	mA
Collector Cutoff Current						
2N6040, 2N6043 2N6041, 2N6044 2N6042, 2N6045	I <sub>CBO</sub>	$V_{CB}$ =60V, $I_{E}$ =0V $V_{CB}$ =80V, $I_{E}$ =0 $V_{CB}$ =100V, $I_{E}$ =0			0.5 0.5 0.5	mA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =5.0V, I <sub>C</sub> =0			2.0	mA
ON CHARACTERISTICS 1				I	I	
DC Current Gain 2N6040,41,43,44 2N6042,45 All types	h <sub>FE</sub>	I <sub>C</sub> =4.0 A, V <sub>CE</sub> =4.0V I <sub>C</sub> =3.0 A, V <sub>CE</sub> =4.0V I <sub>C</sub> =8.0 A, V <sub>CE</sub> =4.0V	1000 1000 100		20000 20000	
Collector-Emitter Sustaining Voltage <sup>1</sup>		-				
2N6040,41,43,44 2N6042,45 All types	$V_{CE(sat)}$	$I_{C}$ =4.0 A, $I_{B}$ =16 mA $I_{C}$ =3.0 A, $I_{B}$ =12 mA $I_{C}$ =8.0 A, $I_{B}$ =80 mA			2.0 2.0 4.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I <sub>C</sub> =8.0 A, I <sub>B</sub> =80 mA			4.5	V

# Note:

1. Pulse Test width = 300  $\mu s$  , Duty Cycle < 2.0%

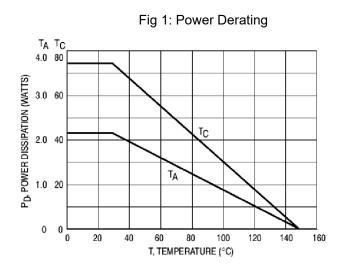






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# TYPICAL CHARACTERISTICS CURVES



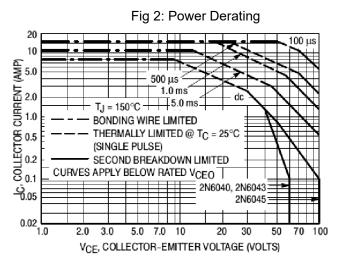


Fig 3:Thermal Response

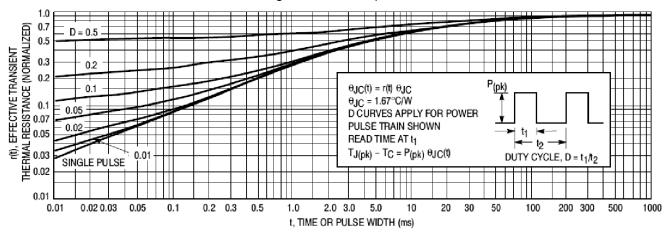


Fig 4: Switching Times Equivalent Circuit

5.0 3.0 2.0 1.0 TIME (µs) 0.7 0.5 0.3  $V_{CC} = 30 \text{ V}$ 0.2 I<sub>C</sub>/I<sub>B</sub> = 250 I<sub>B1</sub> = I<sub>B2</sub> T<sub>J</sub> = 25°C 0.1 PNP NPN 0.07 td @ VBE(off) 0.05 0.5 0.7 1.0 0.2 0.3 2.0 5.0 7.0 0.1 IC, COLLECTOR CURRENT (AMP)

Fig 5: Switching Times

V<sub>CC</sub> -30 V RB & RC VARIED TO OBTAIN DESIRED CURRENT LEVELS D<sub>1</sub> MUST BE FAST RECOVERY TYPE, eg: 1N5825 USED ABOVE IB ≈ 100 mA MSD6100 USED BELOW I<sub>B</sub> ≈ 100 mA SCOPE TUT V<sub>2</sub> approx +8.0 V = 8.0 k  $V_1$ +4.0 V approx for  $\mathbf{t}_{\mathbf{d}}$  and  $\mathbf{t}_{\mathbf{r}}$ ,  $\mathbf{D}_{\mathbf{1}}$  is disconnected

For NPN test circuit reverse all polarities and D1.

 $t_f$ ,  $t_f \le 10 \text{ ns}$ DUTY CYCLE = 1.0%



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# TYPICAL CHARACTERISTICS CURVES

Fig 6: Small-Signal Current Gain 10,000 5000 h<sub>fe</sub>, SMALL-SIGNAL CURRENT GAIN 3000 2000 1000 500 T<sub>C</sub> = 25°C 300 200 VCE = 4.0 Vdc IC = 3.0 Adc 100 50 PNP 30 20 NPN 5.0 20 100 200 500 1000 f, FREQUENCY (kHz)

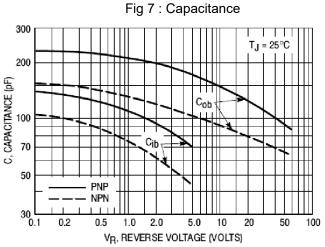
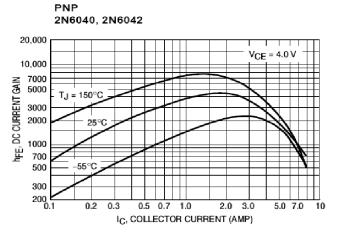
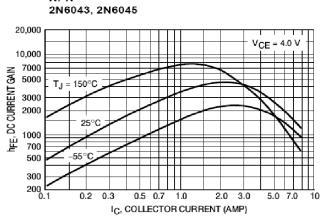


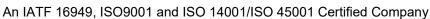
Fig 8: DC Current Gain







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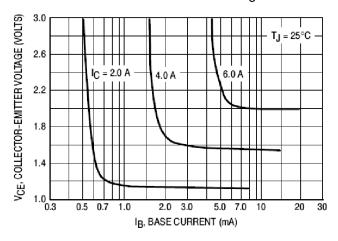






# **TYPICAL CHARACTERISTICS CURVES**

Fig 9: Collector Saturation Region



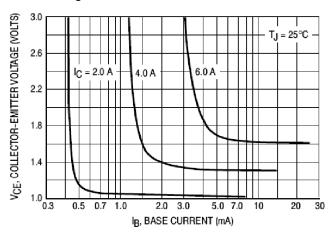
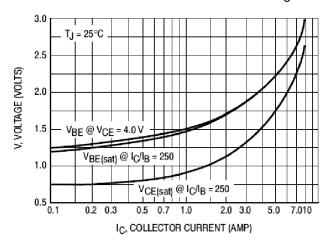
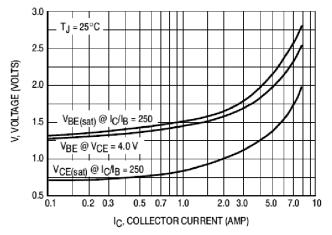


Fig 10: "On" Voltages





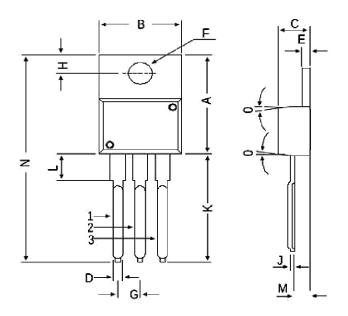






# **PACKAGE DETAILS**

# TO-220 Leaded Plastic Package

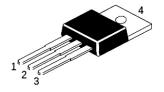


DIM	MIN	MAX
Α	14.42	16.51
В	9.63	10.67
С	3.56	4.83
D	1	0.90
Е	1.15	1.40
F	3.75	3.80
G	2.29	2.79
Н	2.54	3.43
J	-	0.56
K	12.70	14.73
L	2.80	4.07
М	2.03	2.92
Ν		31.24
0	7	7°

All Dimensions are in mm

# **PIN CONFIGURATION**

- 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR







### **Recommended Reflow Solder Profiles**

The recommended reflow solder profiles for Pb and Pb-free devices are shown below.

Figure 1 shows the recommended solder profile for devices that have Pb-free terminal plating, and where a Pb-free solder is used.

Figure 2 shows the recommended solder profile for devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with a leaded solder.

Figure 1

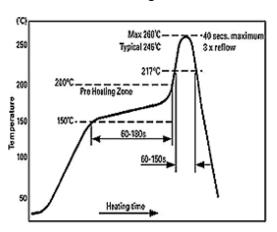
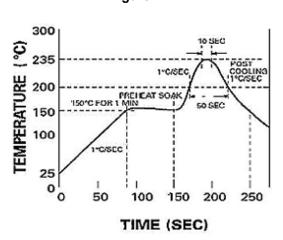


Figure 2



### Reflow profiles in tabular form

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Profile Feature	Sn-Pb System	Pb-Free System		
Average Ramp-Up Rate	~3°C/second	~3°C/second		
Preheat  - Temperature Range	150-170°C	150-200°C		
– Time	60-180 seconds	60-180 seconds		
Time maintained above:  – Temperature  – Time	200°C 30-50 seconds	217°C 60-150 seconds		
Peak Temperature	235°C	260°C max.		
Time within +0 -5°C of actual Peak	10 seconds	40 seconds		
Ramp-Down Rate	3°C/second max.	6°C/second max.		

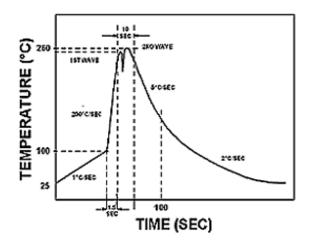


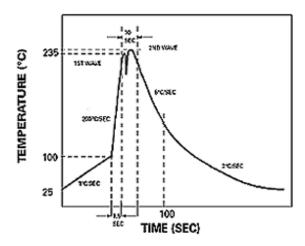


#### **Recommended Wave Solder Profiles**

The Recommended solder Profile For Devices with Pb-free terminal plating where a Pb-free solder is used

The Recommended solder Profile For Devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with leaded solder





### **Wave Profiles in Tabular Form**

Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~200°C/second	~200°C/second
Heating rate during preheat	Typical 1-2, Max 4°C/sec	Typical 1-2, Max 4°C/Sec
Final preheat Temperature	Within 125°C of Solder Temp	Within 125°C of Solder Temp
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	10 seconds
Ramp-Down Rate	5°C/second max.	5°C/second max





# Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- · Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- · Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- · Mechanical stress such as vibration and impact shall be avoided.
- · The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

### **Shelf Life of CDIL Products**

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

#### Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

JEDEC MSL Level			
Level	Time	Condition	
1	Unlimited	≤30 °C / 85% RH	
2	1 Year	≤30 °C / 60% RH	
2a	4 Weeks	≤30 °C / 60% RH	
3	168 Hours	≤30 °C / 60% RH	
4	72 Hours	≤30 °C / 60% RH	
5	48 Hours	≤30 °C / 60% RH	
5a	24 Hours	≤30 °C / 60% RH	
6	Time on Label(TOL)	≤30 °C / 60% RH	







### **Customer Notes**

### **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

#### Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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